

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Complete if Known

Application No.	10/661,037
Filing Date	September 12, 2003
First Named Inventor	John D. Hyde
Art Unit	2822
Examiner Name	Ida M. Soward
Attorney Docket Number	22524-17802

Sheet 1 of 6

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Examiner Initials*	Cite No. ¹	Document No. Number – Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
	A1	US-7,548,460	06-16-2009	Diorio et al.
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	A9	US-6,384,451	05-07-2002	Caywood
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	A60	US-4,822,750	04-18-1989	Perlegos
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	B1	JP 2005-533372	11-04-2005	Impinj, Inc.	
	B2	JP 29-51605	03-10-1998	Programmable Microelectron Co.	
	B3	EP 0 562 257 A1	09-29-1993	International Business Machines Corporation	
	B4	WO 00/60672 A1	10-12-2000	Koninklijke Philips Electronics N.V.	
	B5	WO 00/38239 A1	06-29-2000	Lattice Semiconductor Corporation	

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	C2	ARITOME, S. et al., "Reliability Issues of Flash Memory Cells," Proceedings of the IEEE, May 1993, pp. 776-787, Vol. 81, No. 5.	
	C3	BARAFF, G.A., "Distribution Functions and Ionization Rates for Hot Electrons in Semiconductors," Short-Range Order Effect on Magnetic Anisotropy, Physical Review, December 15, 1962, pp. 2507-2517, Vol. 128, No. 6.	
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OTHER REFERENCES – NON-PATENT LITERATURE DOCUMENTS

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